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Vishay Semiconductors

## **Thyristor Surface Mount, Phase Control SCR, 16 A**



D <sup>2</sup> PAK	TO	つにつり	۱D
D-PAN		-というド	<b>\D</b>

PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	16 A						
$V_{DRM}/V_{RRM}$	1600 V						
V <sub>TM</sub>	1.25 V						
I <sub>GT</sub>	45 mA						
T <sub>J</sub>	-40 to +125 °C						
Package	D <sup>2</sup> PAK (TO-263AB)						
Circuit configuration	Single SCR						

### **FEATURES**

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C



 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### **APPLICATIONS**

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-25TTS16S-M3 of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 µm) copper	3.5	5.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	16.5	25.0							

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	16	A						
I <sub>RMS</sub>		25	A						
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V						
I <sub>TSM</sub>		350	Α						
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
T <sub>J</sub>		-40 to +125	°C						

<b>VOLTAGE RATINGS</b>			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> , AT 125 °C mA
VS-25TTS16S-M3	1600	1600	10



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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEC	T CONDITIONS	VAL	UES	UNITS		
PANAMETEN	STIVIBUL	31MBOL TEST CONDITIONS				UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	onduction half sine wave	1	6			
Maximum RMS on-state current	I <sub>RMS</sub>			2	25	Α		
Maximum peak, one-cycle,	l	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	3	00	^		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, r	10 ms sine pulse, no voltage reapplied					
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	450		A <sup>2</sup> s		
waxiinum i-t ior iusing	1-1	10 ms sine pulse, r	630		A-5			
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms	t = 0.1 ms to 10 ms, no voltage reapplied					
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C	16 A, T <sub>J</sub> = 25 °C			V		
On-state slope resistance	r <sub>t</sub>	T 105 °C		12.0		mΩ		
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1.0		V		
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	V = roted V = A/	0	.5			
waximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = rated V <sub>RRM</sub> /V <sub>DRM</sub>	10				
Holding current	lΗ	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C			200			
Maximum rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> max., linear	r to 80 %, $V_{DRM} = R_g - k = open$	50	00	V/µs		
Maximum rate of rise of turned-on current	dl/dt			150		A/µs		

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P <sub>GM</sub>		8.0	W				
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV				
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α				
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = -10  ^{\circ}\text{C}$	60	mA				
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25$ °C	45					
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	20					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	2.5					
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0 V					
		Anode supply = 6 V, resistive load, $T_J = 125  ^{\circ}\text{C}$	1.0	V				
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = reted value	0.25					
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	2.0	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	4	μs				
Typical turn-off time	t <sub>q</sub>	1j=120 C	110					



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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> (1)		40	C/VV				
Approximate weight			2	g				
Approximate weight			0.07	OZ.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TT	S16S				

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

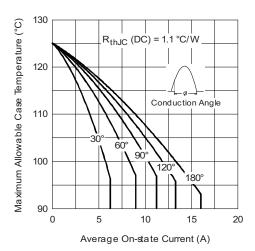


Fig. 1 - Current Rating Characteristics

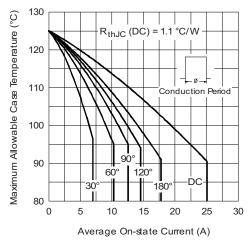


Fig. 2 - Current Rating Characteristics

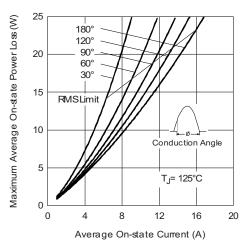


Fig. 3 - On-State Power Loss Characteristics

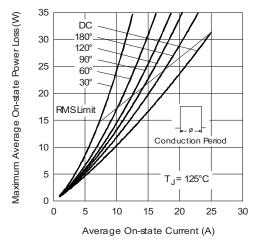


Fig. 4 - On-State Power Loss Characteristics

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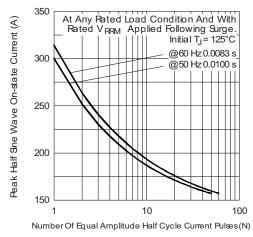


Fig. 5 - Maximum Non-Repetitive Surge Current

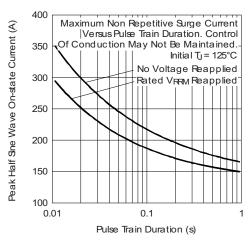


Fig. 6 - Maximum Non-Repetitive Surge Current

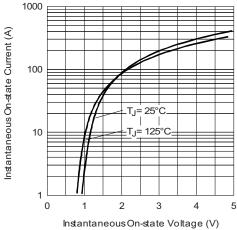


Fig. 7 - On-State Voltage Drop Characteristics

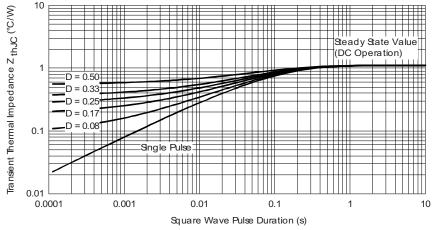


Fig. 8 - Gate Characteristics

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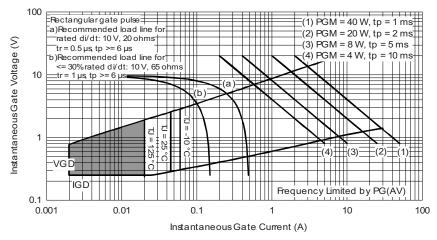


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

#### **ORDERING INFORMATION TABLE**

Device code VS-S S **TRL** 25 Т Т 16 -M3 (7)(2)(3) (4) (5) (6) (8) 9 Vishay Semiconductors product Current rating (25 = 25 A) Circuit configuration: T = single thyristor Package:  $T = D^2PAK (TO-263AB)$ 5 Type of silicon: S = standard recovery rectifier Voltage rating: Voltage code x  $100 = V_{RRM}$ 16 = 1600 V S = surface mountable • None = tube • TRL = tape and reel (left oriented) TRR = tape and reel (right oriented) 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS16S-M3	50	1000	Antistatic plastic tubes					
VS-25TTS16STRR-M3	800	800	13" diameter reel					
VS-25TTS16STRL-M3	800	800	13" diameter reel					

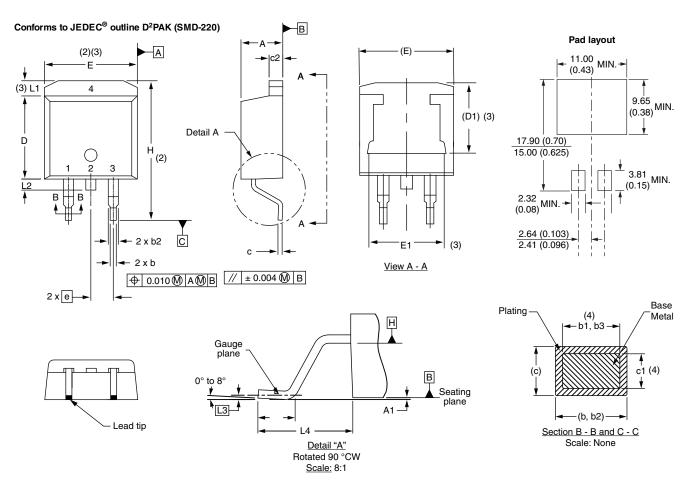
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



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### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 **1** Document Number: 96164



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